



SANYO Semiconductors

DATA SHEET

2SB926 / 2SD1246

PNP / NPN Epitaxial Planar Silicon Transistors
Large-Current Driving Applications

Applications

- Power supplies, relay drivers, lamp drivers, electrical equipment.

Features

- Adoption of FBET, MBIT processes.
- Low saturation voltage.
- Large current capacity and wide ASO.

Specifications () : 2SB926

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CB0}		(-)30	V
Collector-to-Emitter Voltage	V _{CEO}		(-)25	V
Emitter-to-Base Voltage	V _{EBO}		(-)6	V
Collector Current	I _C		(-)2	A
Collector Current (Pulse)	I _{CP}		(-)5	A
Collector Dissipation	P _C		0.75	W
Junction Temperature	T _J		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I _{CBO}	V _{CB} =(-)20V, I _E =0A			(-)0.1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =(-)4V, I _C =0A			(-)0.1	μA
DC Current Gain	h _{FE1}	V _{CE} =(-)2V, I _C =(-)100mA	100*		560*	
	h _{FE2}	V _{CE} =(-)2V, I _C =(-)1.5A, pulse	65	130		
Gain-Bandwidth Product	f _T	V _{CE} =(-)10V, I _C =(-)50mA		150		MHz
Output Capacitance	C _{ob}	V _{CB} =(-)10V, f=1MHz		(32)19		pF

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* : The 2SB926 / 2SD1246 are classified by 100mA h_{FE} as follows :

Rank	R	S	T	U
h _{FE}	100 to 200	140 to 280	200 to 400	280 to 560

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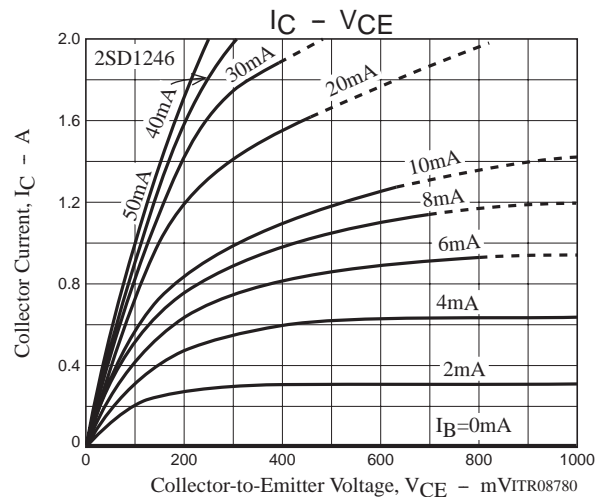
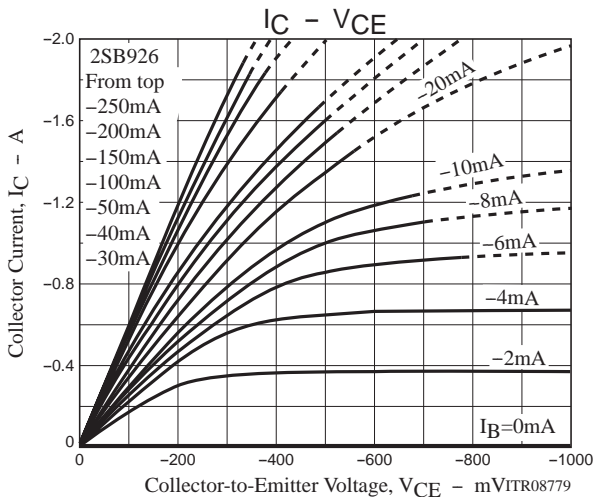
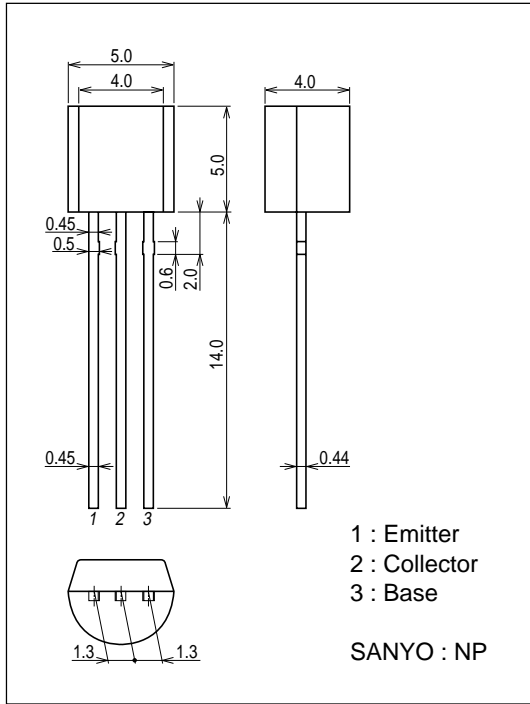
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)1.5A, I_B=(-)75mA, \text{ pulse}$		(-0.35)0.18	(-0.6)0.4	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)1.5A, I_B=(-)75mA$		(-0.85)	(-1.2)	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0A$	(-)30			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1mA, R_{BE}=\infty$	(-)25			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu A, I_C=0A$	(-)6			V

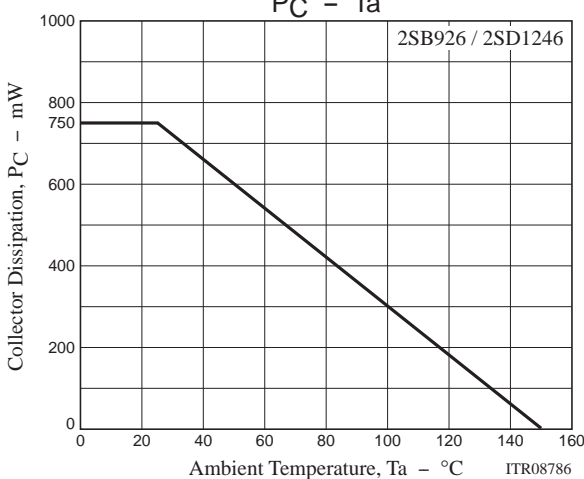
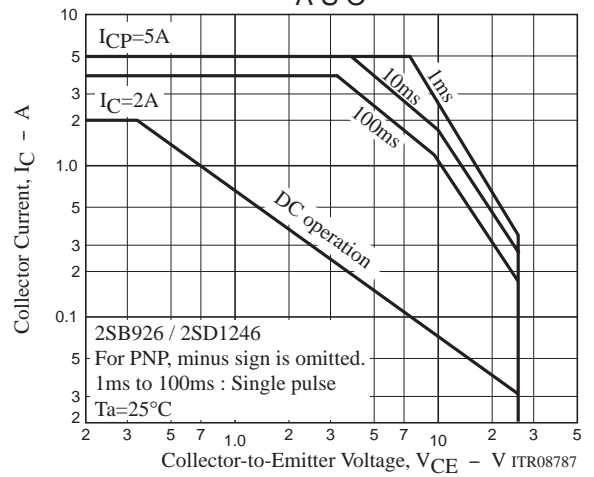
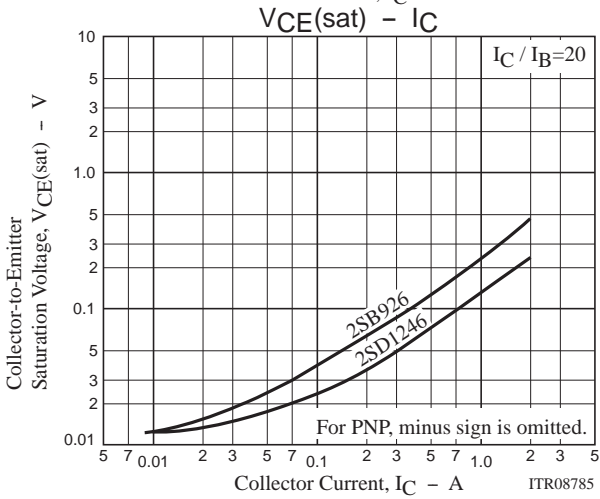
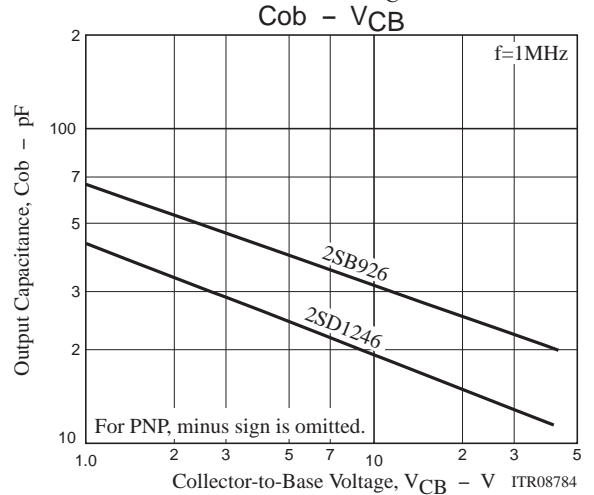
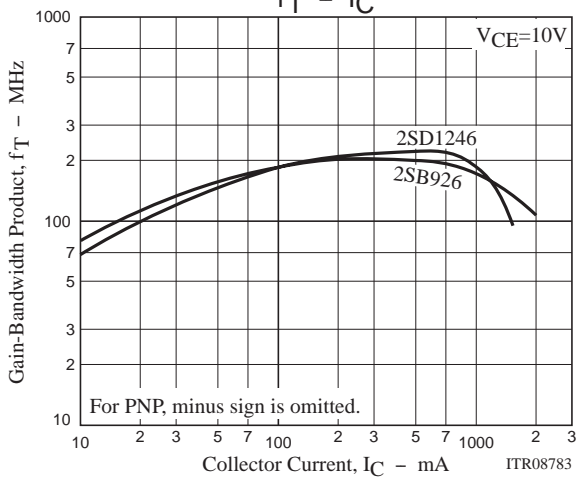
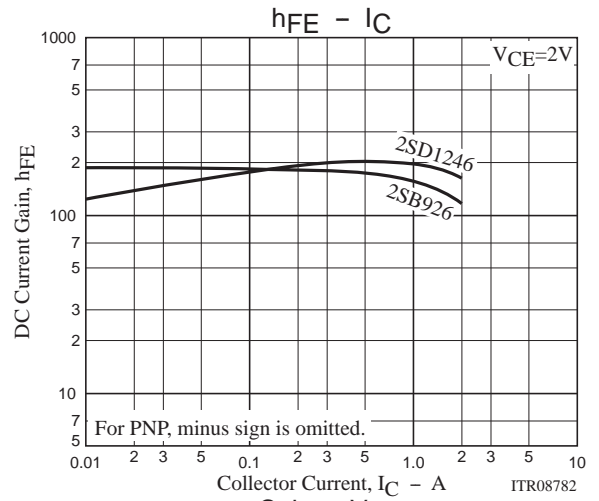
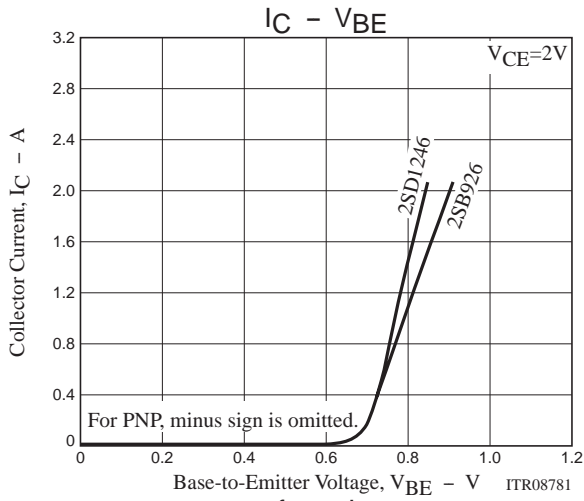
Package Dimensions

unit : mm (typ)

7522-002



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